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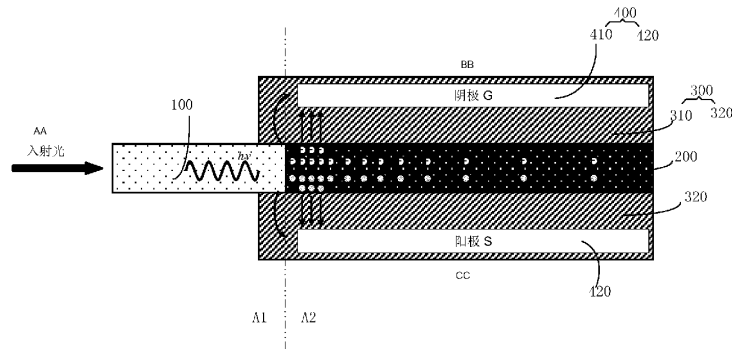
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(81) 指定国(除另有指明, 要求每一种可提供的国家保护): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW。

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(54) Title: PHOTOELECTRIC DETECTOR AND OPTICAL CHIP

(54) 发明名称: 光电探测器以及光芯片



[图1]

AA Incident light
BB Cathode
CC Anode

(57) Abstract: The present application relates to a photoelectric detector and an optical chip. The photoelectric detector comprises: a light guide part, located in the first area and used for conducting incident light; an absorption part, located in a second area connected to the first area, connected to the light guide part and used for absorbing incident light and generating photon-generated carriers; a semiconductor conductive part, comprising an N-type conductive part and a P-type conductive part, the N-type conductive part and the P-type conductive part being located on the two sides of the absorption part, respectively; and an electrode part, comprising a cathode and an anode, the cathode being connected to the N-type conductive part, and the anode being connected to the P-type conductive part. A conductive area between the absorption part and the electrode part extends from the second area to the first area. According to embodiments of the present application, the performance of the photoelectric detector can be effectively improved.

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HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO,
PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF,
CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN,
TD, TG)。

根据细则4.17的声明:

- 关于发明人身份(细则4.17(i))
- 关于申请人有权申请并被授予专利(细则4.17(ii))
- 发明人资格(细则4.17(iv))

本国际公布:

- 包括国际检索报告(条约第21条(3))。

(57) 摘要: 本申请涉及一种光电探测器以及光芯片。光电探测器包括: 导光部, 位于第一区, 用于传导入射光; 吸收部, 位于与第一区连接的第二区, 且连接导光部, 用于吸收入射光并产生光生载流子; 半导体导电部, 包括N型导电部以及P型导电部, N型导电部与P型导电部分别位于吸收部两侧; 电极部, 包括阴极以及阳极, 阴极连接N型导电部, 阳极连接P型导电部; 吸收部与电极部之间的导电区域由第二区延伸至第一区。本申请实施例可以有效提高光电探测器性能。